

## ABSTRACT OF THE DISCLOSURE

There is provided a semiconductor device which is capable of solving a  
5 problem of threshold control in CMOS transistor, accompanied with combination  
of a gate insulating film having a high dielectric constant and a metal gate  
electrode, and significantly enhancing performances without deterioration in  
reliability of a device. The semiconductor device includes a gate insulating film  
composed of a material having a high dielectric constant, and a gate electrode.  
10 A portion of the gate electrode making contact with the gate insulating film has a  
composition including silicide of metal M expressed with  $M_xSi_{1-x}$  ( $0 < x < 1$ ), as a  
primary constituent.  $x$  is greater than 0.5 ( $x > 0.5$ ) in a p-type MOSFET, and is  
equal to or smaller than 0.5 ( $x \leq 0.5$ ) in a n-type MOSFET.